

# Silicon Carbide (SiC) MOSFET - EliteSiC, 32 mohm, 650 V, M3S, TO247-4L

## NTH4L032N065M3S

### Features

- Typical  $R_{DS(ON)} = 32\text{ m}\Omega @ V_{GS} = 18\text{ V}$
- Ultra Low Gate Charge ( $Q_{G(tot)} = 55\text{ nC}$ )
- High Speed Switching with Low Capacitance ( $C_{OSS} = 114\text{ pF}$ )
- 100% Avalanche Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

### Applications

- SMPS, Solar Inverters, UPS, Energy Storage, EV Charging Infrastructure

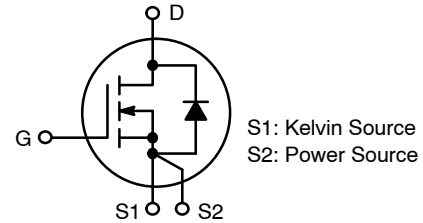
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	650	V
Gate-to-Source Voltage	$V_{GS}$	-8/+22	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	$I_D$	50 A
Power Dissipation		$P_D$	187 W
Continuous Drain Current (Note 1)	$T_C = 100^\circ\text{C}$	$I_D$	30 A
Power Dissipation		$P_D$	94 W
Pulsed Drain Current (Note 2)	$T_C = 25^\circ\text{C}, t_p = 100\text{ }\mu\text{s}$	$I_{DM}$	163 A
Continuous Source-Drain Current (Body Diode)	$T_C = 25^\circ\text{C}, V_{GS} = -3\text{ V}$	$I_S$	29 A
	$T_C = 100^\circ\text{C}, V_{GS} = -3\text{ V}$		16
Pulsed Source-Drain Current (Body Diode) (Note 2)	$T_C = 25^\circ\text{C}, V_{GS} = -3\text{ V}, t_p = 100\text{ }\mu\text{s}$	$I_{SM}$	137 A
Single Pulse Avalanche Energy ( $I_{LPK} = 16.7\text{ A}, L = 1\text{ mH}$ ) (Note 3)	$E_{AS}$	139	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$
Lead Temperature for Soldering Purposes (1/8" from case for 10 secs)	$T_L$	270	$^\circ\text{C}$

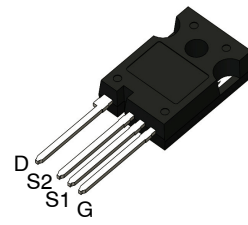
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. 30 A is limited by package. Power chip max drain current is 35 A if limited by max junction temperature.
2. Single pulse, limited by max junction temperature.
3.  $E_{AS}$  of 139 mJ is based on starting  $T_J = 25^\circ\text{C}, L=1\text{ mH}, I_{AS}=16.7\text{ A}, V_{DD} = 100\text{ V}, V_{GS} = 18\text{ V}$ .

$V_{(BR)DSS}$	$R_{DS(ON)}$ TYP	$I_D$ MAX
650 V	32 m $\Omega$ @ 18 V	50 A



N-CHANNEL MOSFET



TO-247-4L  
CASE 340CJ

### MARKING DIAGRAM



H4L032065M3S = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

Device	Package	Shipping
NTH4L032N065M3S	TO-247-4L	30 Units / Tube

# NTH4L032N065M3S

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Note 4)	$R_{\theta JC}$	0.80	°C/W
Thermal Resistance, Junction-to-Ambient (Note 4)	$R_{\theta JA}$	40	

4. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

## RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value	Unit
Operation Values of Gate-to-Source Voltage	$V_{GSop}$	-5...-3/+18	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	650	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$ , Referenced to $25^\circ\text{C}$	-	90	-	mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650\text{ V}, T_J = 25^\circ\text{C}$	-	-	10	$\mu\text{A}$
		$V_{DS} = 650\text{ V}, T_J = 175^\circ\text{C}$ (Note 6)	-	-	500	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = -8/+22\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 1.0$	$\mu\text{A}$

## ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 18\text{ V}, I_D = 15\text{ A}, T_J = 25^\circ\text{C}$	-	32	44	m $\Omega$
		$V_{GS} = 18\text{ V}, I_D = 15\text{ A}, T_J = 175^\circ\text{C}$ (Note 6)	-	49	-	
		$V_{GS} = 15\text{ V}, I_D = 15\text{ A}, T_J = 25^\circ\text{C}$	-	41	-	
		$V_{GS} = 15\text{ V}, I_D = 15\text{ A}, T_J = 175^\circ\text{C}$ (Note 6)	-	52	-	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 7.5\text{ mA}, T_J = 25^\circ\text{C}$	2.0	2.9	4.0	V
Forward Transconductance	$g_{FS}$	$V_{DS} = 10\text{ V}, I_D = 15\text{ A}$ (Note 6)	-	9.9	-	S

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ (Note 6)	-	1410	-	pF
Output Capacitance	$C_{OSS}$		-	114	-	
Reverse Transfer Capacitance	$C_{RSS}$		-	9.2	-	
Total Gate Charge	$Q_G(TOT)$	$V_{DD} = 400\text{ V}, I_D = 15\text{ A}, V_{GS} = -3/18\text{ V}$ (Note 6)	-	55	-	nC
Gate-to-Source Charge	$Q_{GS}$		-	15	-	
Gate-to-Drain Charge	$Q_{GD}$		-	14	-	
Gate Resistance	$R_G$	$f = 1\text{ MHz}$	-	5.0	-	$\Omega$

## SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -3/18\text{ V}, V_{DD} = 400\text{ V}, I_D = 15\text{ A}, R_G = 4.7\text{ }\Omega, T_J = 25^\circ\text{C}$ (Notes 5, 6)	-	8.8	-	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	31	-	
Rise Time	$t_r$		-	12	-	
Fall Time	$t_f$		-	9	-	$\mu\text{J}$
Turn-On Switching Loss	$E_{ON}$		-	33	-	
Turn-Off Switching Loss	$E_{OFF}$		-	16	-	
Total Switching Loss	$E_{TOT}$		-	49	-	

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -3/18\text{ V}, V_{DD} = 400\text{ V},$ $I_D = 15\text{ A}, R_G = 4.7\ \Omega, T_J = 175^\circ\text{C}$ (Notes 5, 6)	-	7.8	-	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	37	-	
Rise Time	$t_r$		-	12	-	
Fall Time	$t_f$		-	11	-	
Turn-On Switching Loss	$E_{ON}$		-	31	-	$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$		-	25	-	
Total Switching Loss	$E_{TOT}$		-	56	-	

## SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$I_{SD} = 15\text{ A}, V_{GS} = -3\text{ V}, T_J = 25^\circ\text{C}$	-	4.5	6.0	V
		$I_{SD} = 15\text{ A}, V_{GS} = -3\text{ V}, T_J = 175^\circ\text{C}$ (Note 6)	-	4.2	-	
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -3\text{ V}, I_S = 15\text{ A},$ $di/dt = 1000\text{ A}/\mu\text{s}, V_{DS} = 400\text{ V}$ (Note 6)	-	15.5	-	ns
Charge Time	$t_a$		-	8.9	-	
Discharge Time	$t_b$		-	6.6	-	
Reverse Recovery Charge	$Q_{RR}$		-	72	-	nC
Reverse Recovery Energy	$E_{REC}$		-	4.6	-	$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$		-	9.3	-	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5.  $E_{ON}/E_{OFF}$  result is with body diode.

6. Defined by design, not subject to production test.

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## TYPICAL CHARACTERISTICS

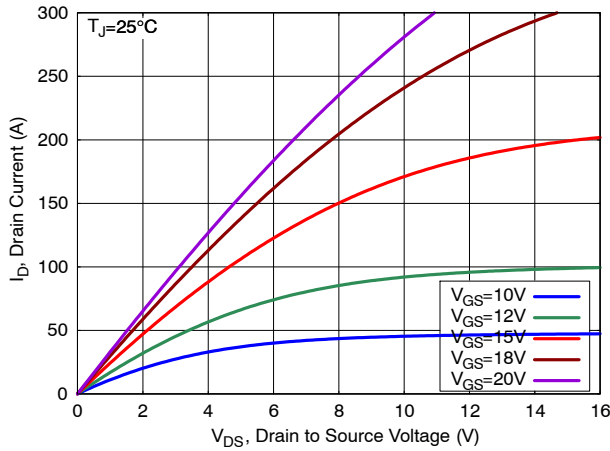


Figure 1. On-Region Characteristics

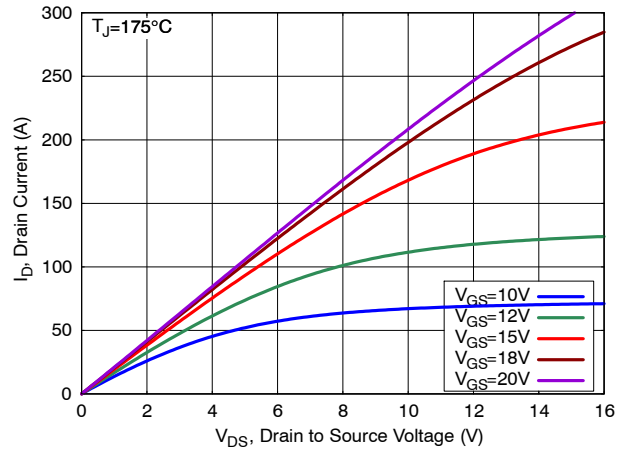


Figure 2. Output Characteristics

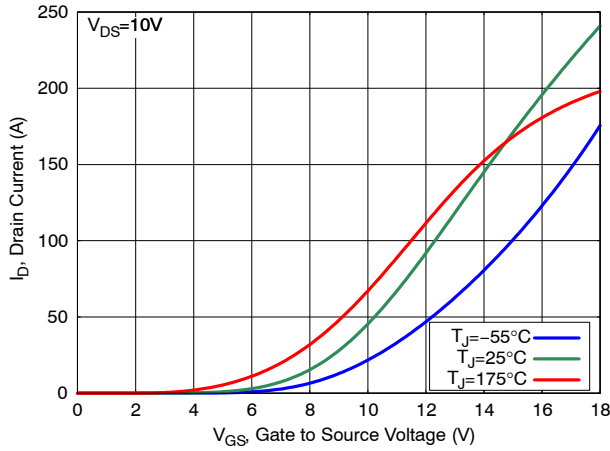


Figure 3. Transfer Characteristics

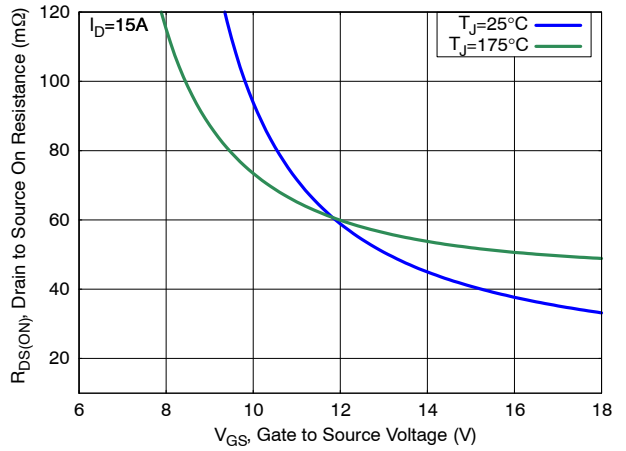


Figure 4. On-Resistance vs. Gate Voltage

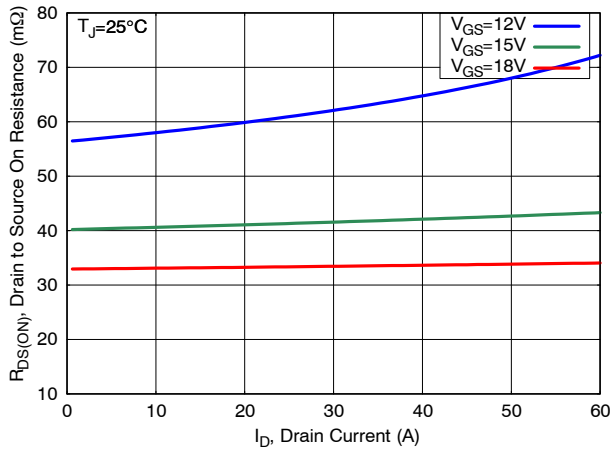


Figure 5. On-Resistance vs. Drain Current

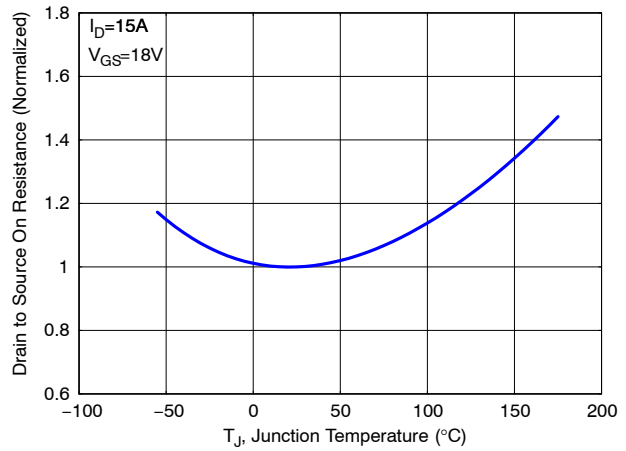


Figure 6. On-Resistance vs. Junction Temperature

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## TYPICAL CHARACTERISTICS

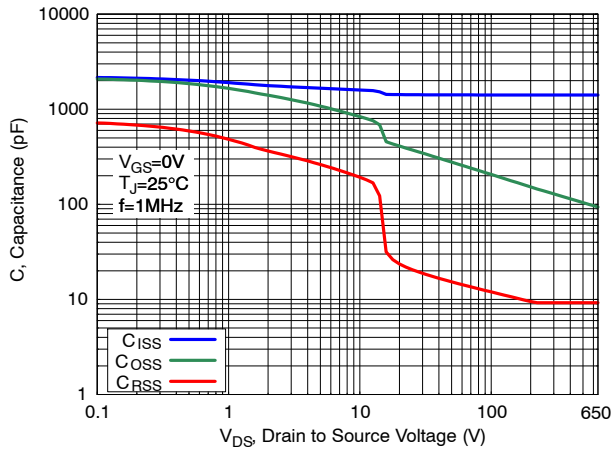


Figure 7. Capacitance Characteristics

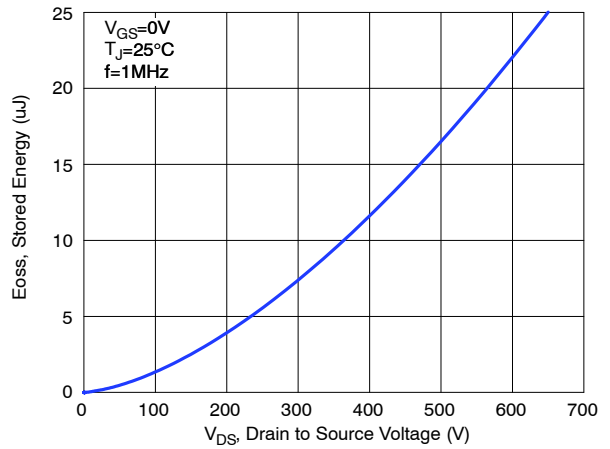


Figure 8. Stored Energy vs. Drain-to-Source Voltage

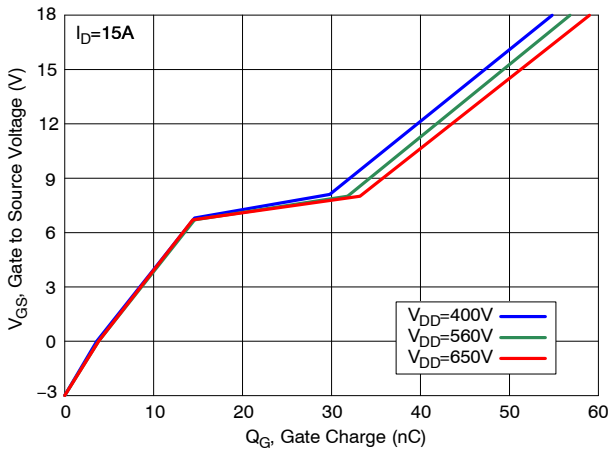


Figure 9. Gate Charge Characteristics

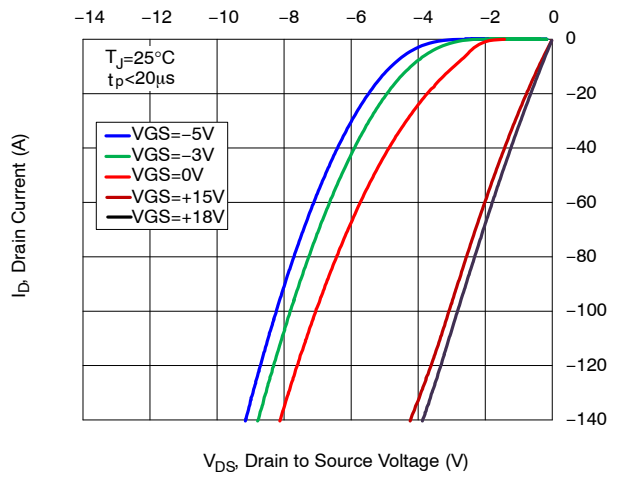


Figure 10. Reverse Conduction Characteristics

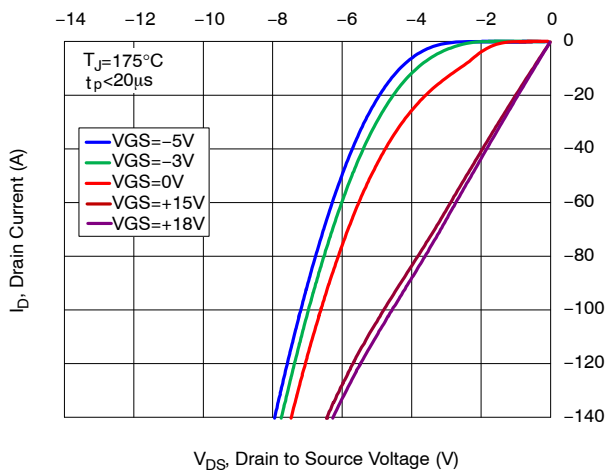


Figure 11. Reverse Conduction Characteristics

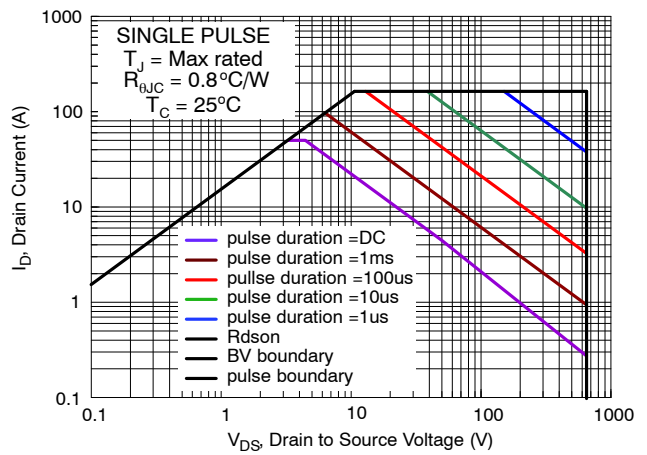
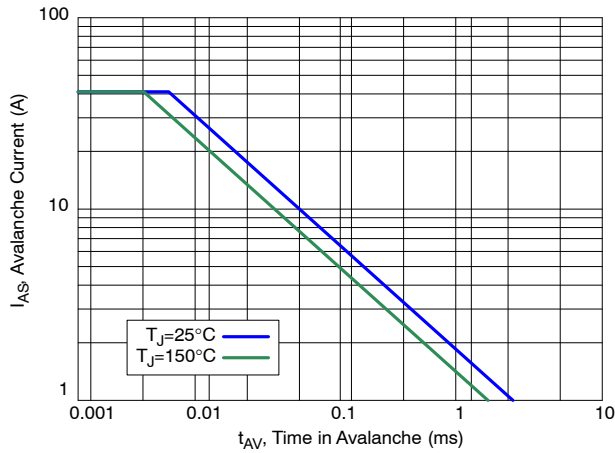


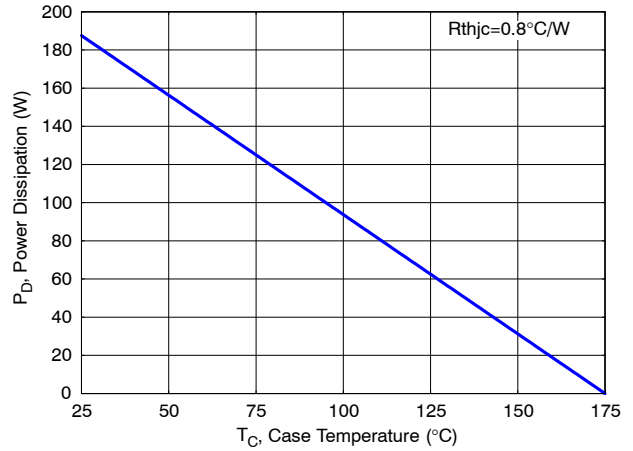
Figure 12. Safe Operating Area

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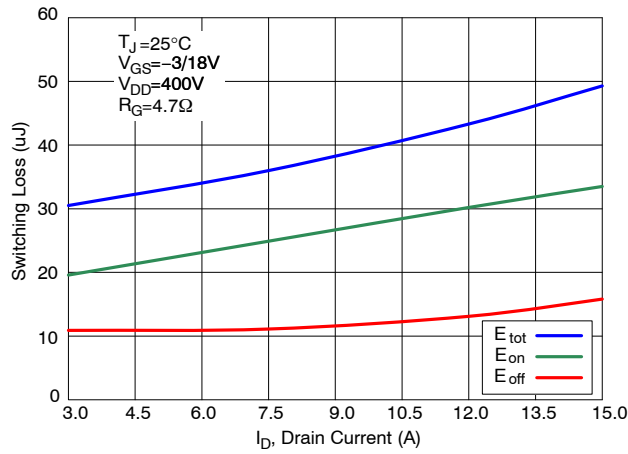
## TYPICAL CHARACTERISTICS



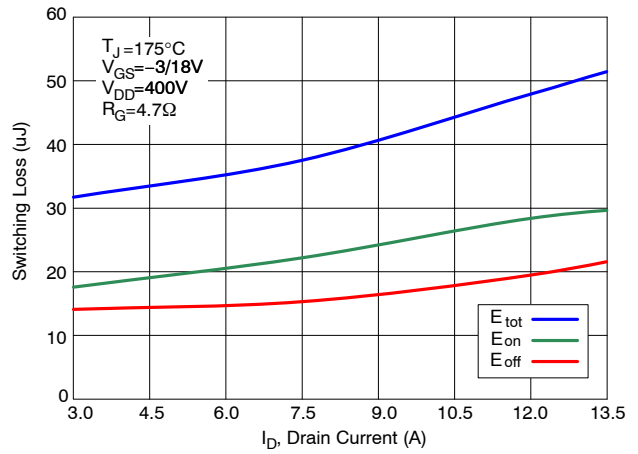
**Figure 13. Avalanche Current vs. Pulse Time (UIS)**



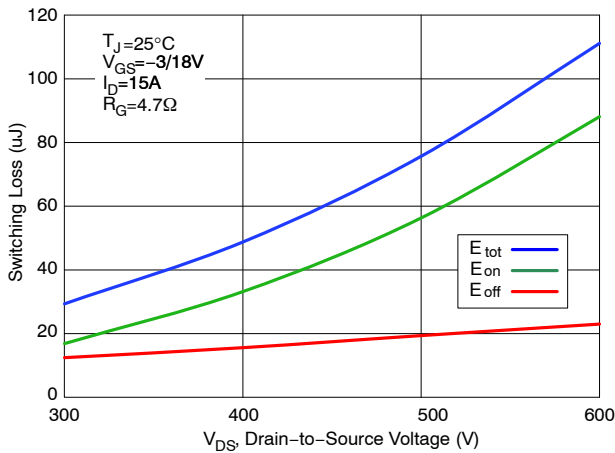
**Figure 14. Maximum Power Dissipation vs. Case Temperature**



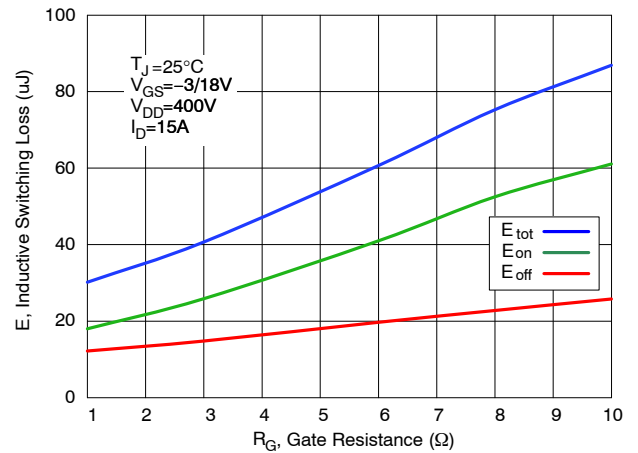
**Figure 15. Inductive Switching Loss vs. Drain Current**



**Figure 16. Inductive Switching Loss vs. Drain Current**



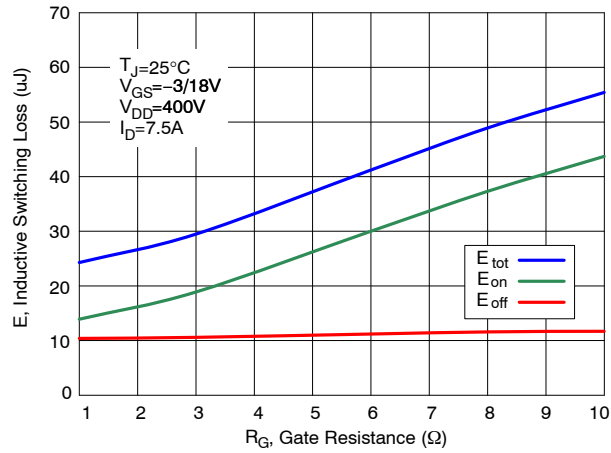
**Figure 17. Inductive Switching Loss vs. Drain Voltage**



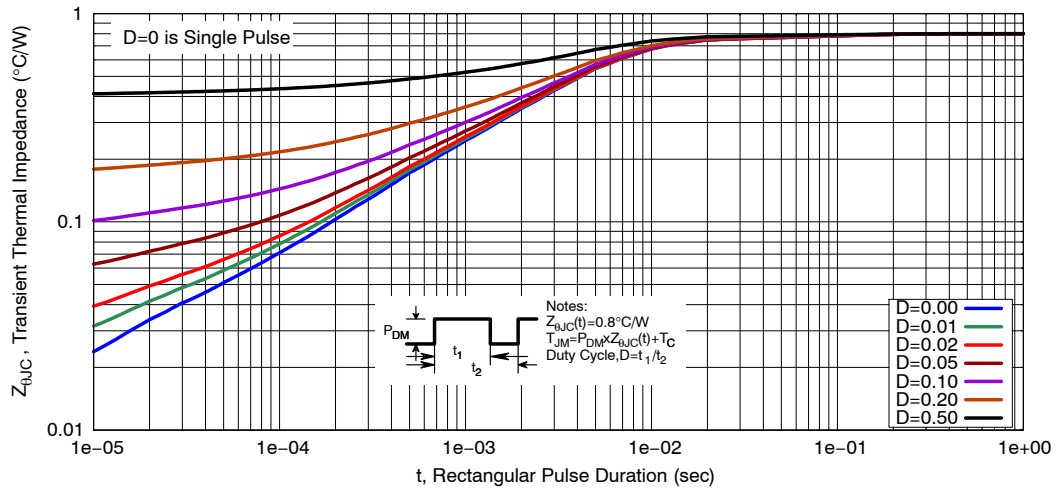
**Figure 18. Inductive Switching Loss vs. Gate Resistance**

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## TYPICAL CHARACTERISTICS



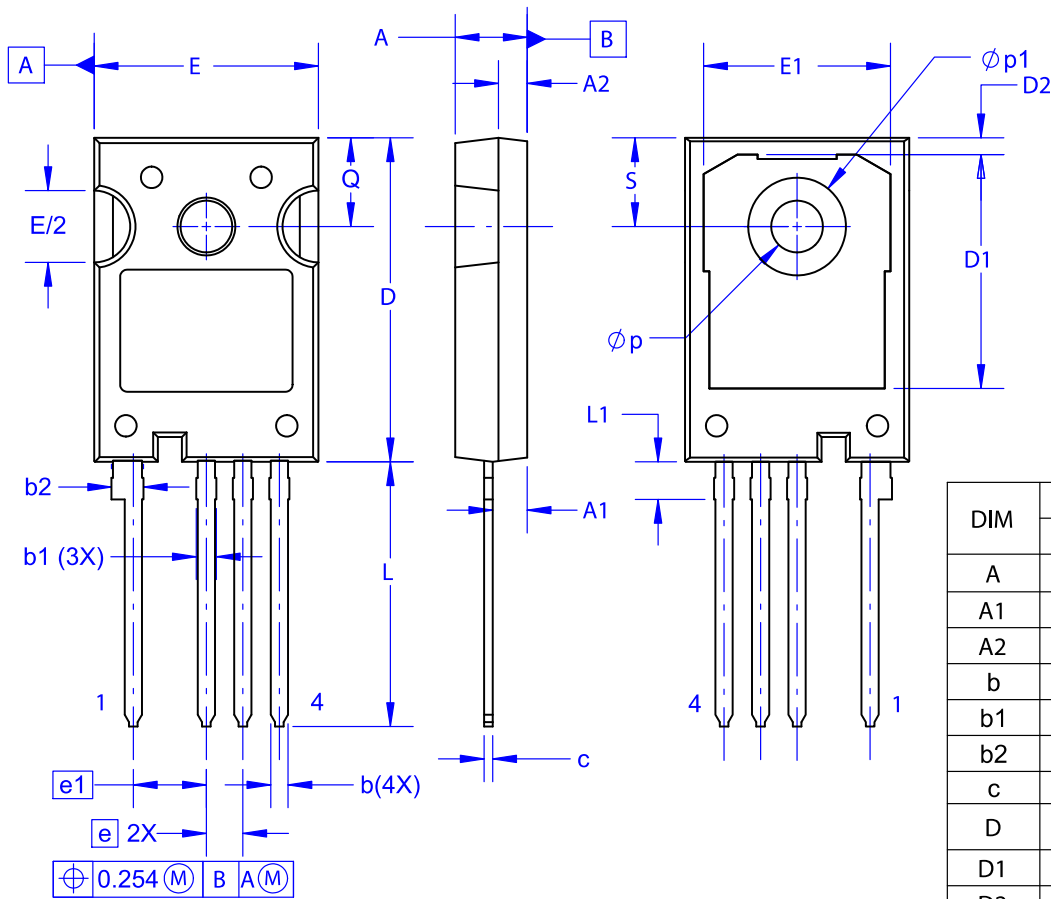
**Figure 19. Inductive Switching Loss vs. Gate Resistance**



**Figure 20. Thermal Response Characteristics**

TO-247-4LD  
CASE 340CJ  
ISSUE A

DATE 16 SEP 2019



NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

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